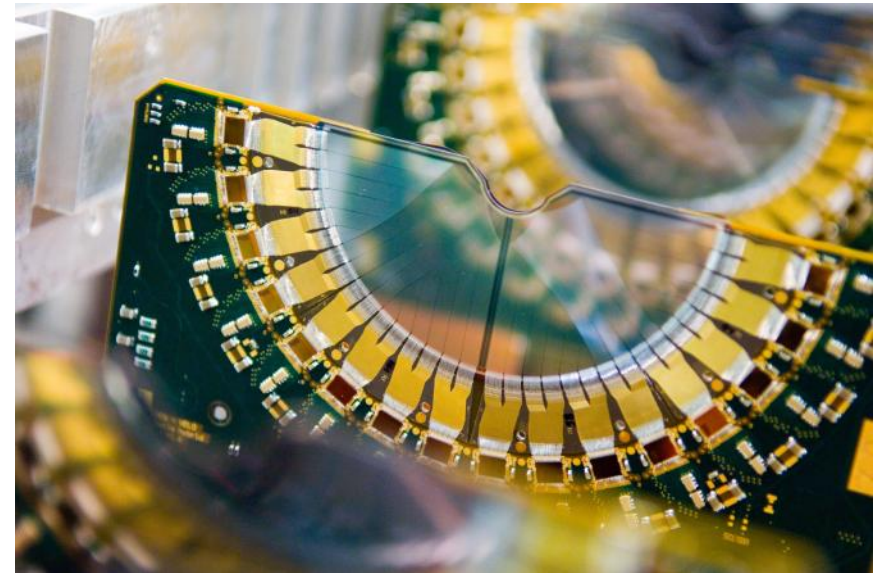


# LHCb VELO: radiation damage

The effects of radiation damage  
on silicon sensors close to the  
LHC beam

7th Workshop on Advanced Silicon  
Radiation Detectors, Ljubljana.  
29 February – 2 March 2012

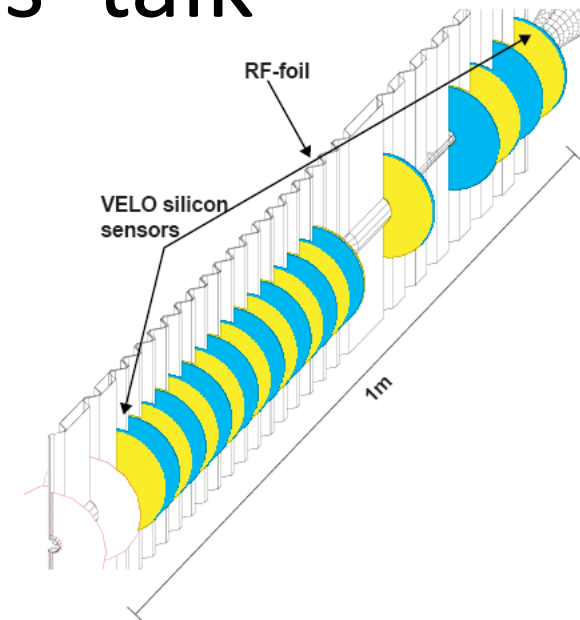


David Hutchcroft  
University of Liverpool  
on behalf of the LHCb collaboration

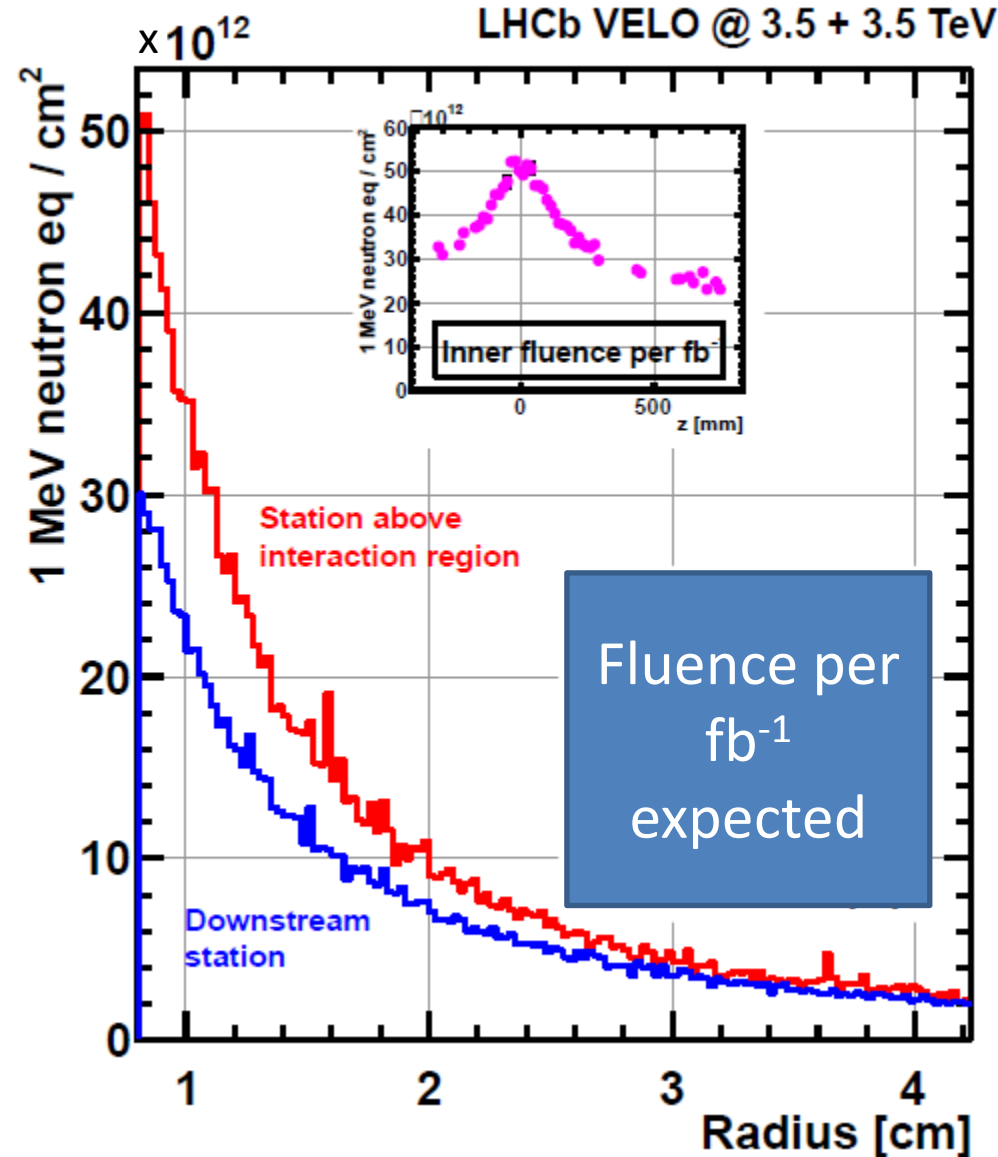
# VELO parameters

for details see Eddy Jans' talk

- 42 modules with pairs of sensors all n-in-n
  - Except one n-in-p (module 0 in later plots)
- R/ $\phi$  geometry strip detector
  - Inner most strips are 8mm from the beam, outer most 42mm from the beam
- Designed to tolerate 5 years running at LHC
  
- Sufficiently radiation hard to be used without modification in a proton therapy beam at Clatterbridge Oncology centre



# Current dose



Currently operating with 7 TeV p-p collisions

Small reduction in expected does per inverse-femtobarn compared to 14 TeV

Collected about  $1.22 \text{ fb}^{-1}$  so far in 2009 to 2011

Both centre-of-mass and luminosities due to increase in 2012

# Radiation effects observed

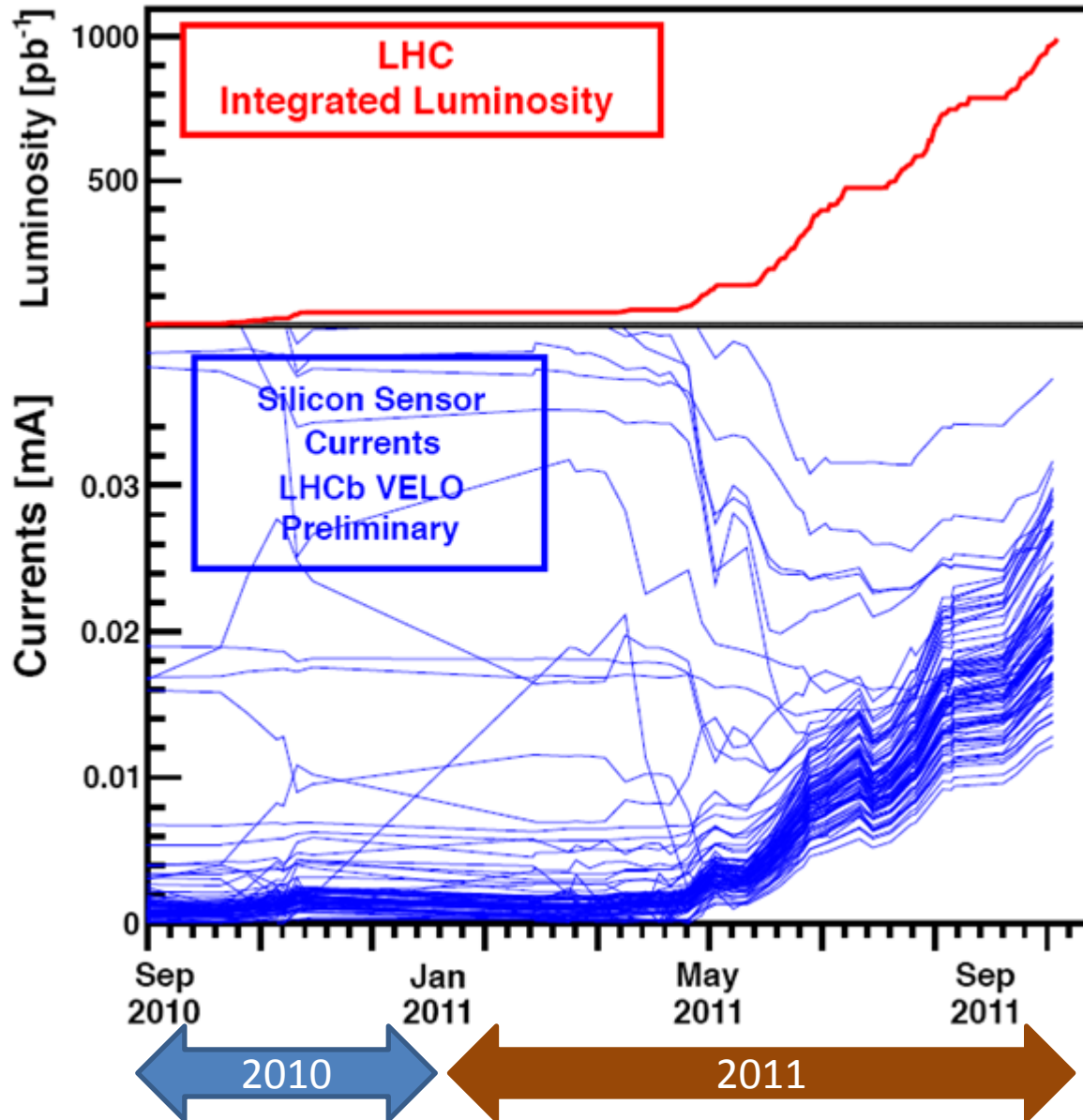
Most direct effect: leakage current increases

Currents measured at approx  $-8^{\circ}\text{C}$  without beam

Typical increase was  $1.9 \mu\text{A}$  per  $100 \text{ pb}^{-1}$

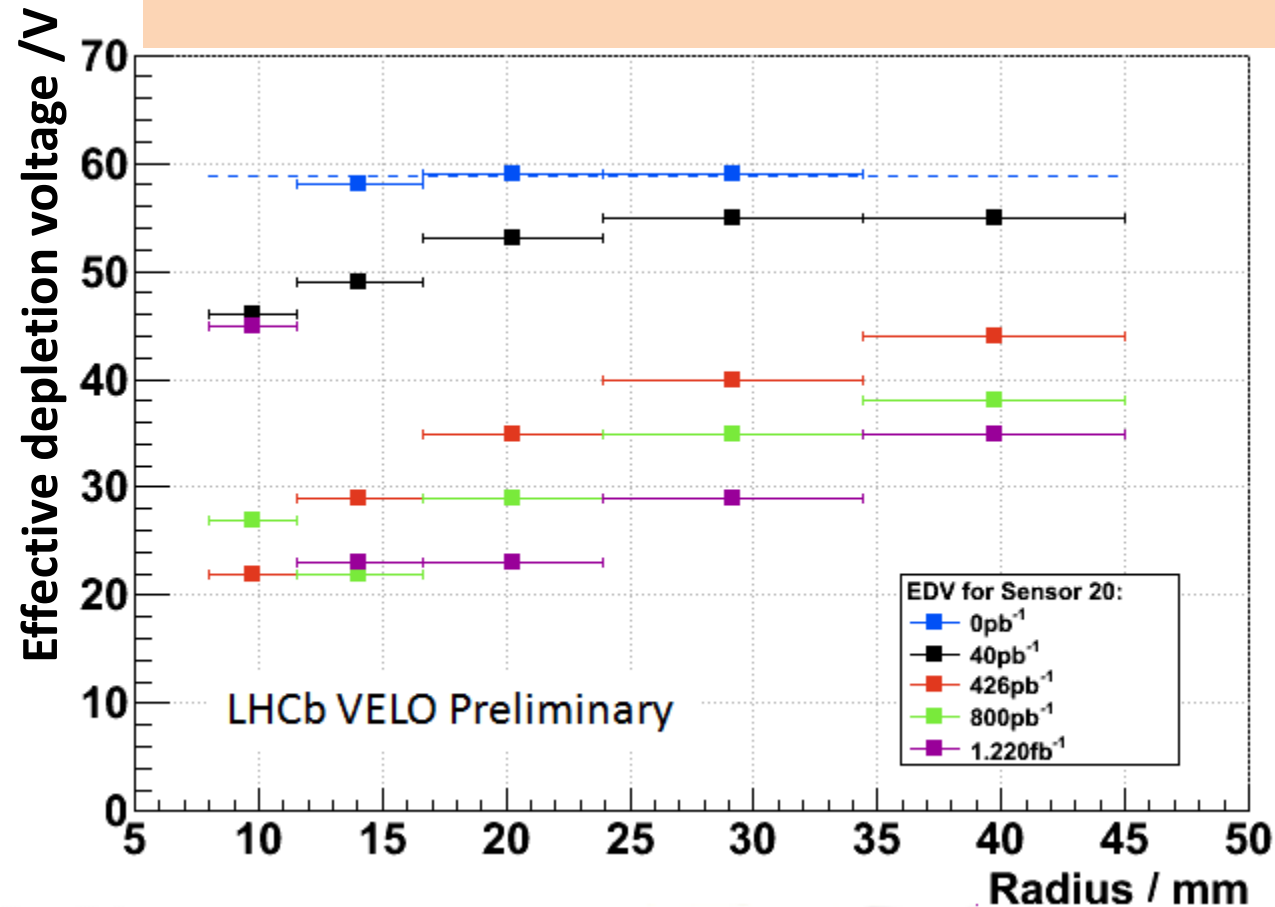
Each line is one sensor's leakage current at 150V

The red line is the integrated luminosity



# How effective depletion voltage for one sensor changes with fluence

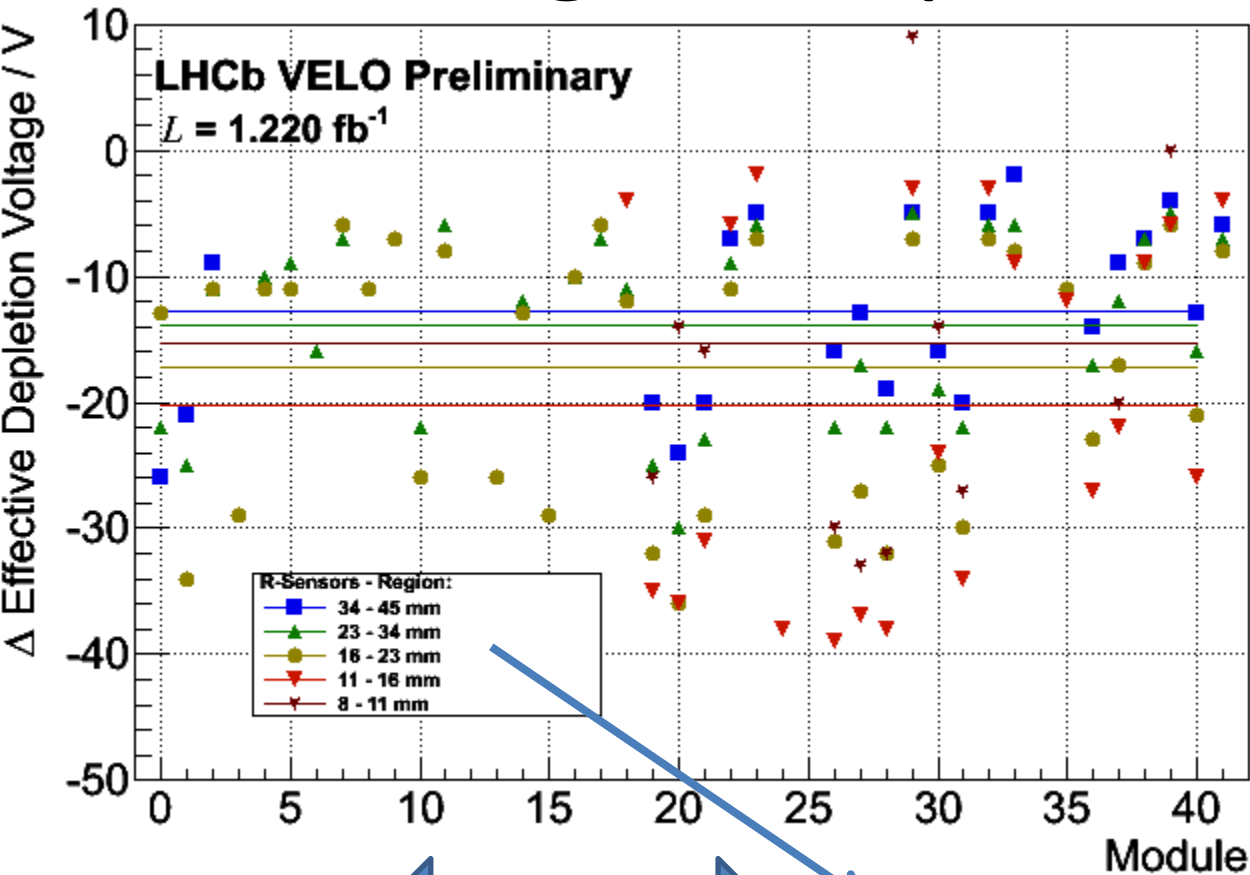
Measure EDV during HV scans in data taking by looking at the charge collection efficiency vs Voltage curves



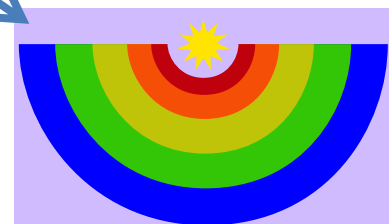
One typical sensor:  
Sensor 20  
n-in-n R-type sensor  
Close to the interaction  
point

Type inversion of n-bulk  
to p-bulk now visible at  
inner radius as EDV starts  
to rise again

# Change in depletion voltage



Highest dose region



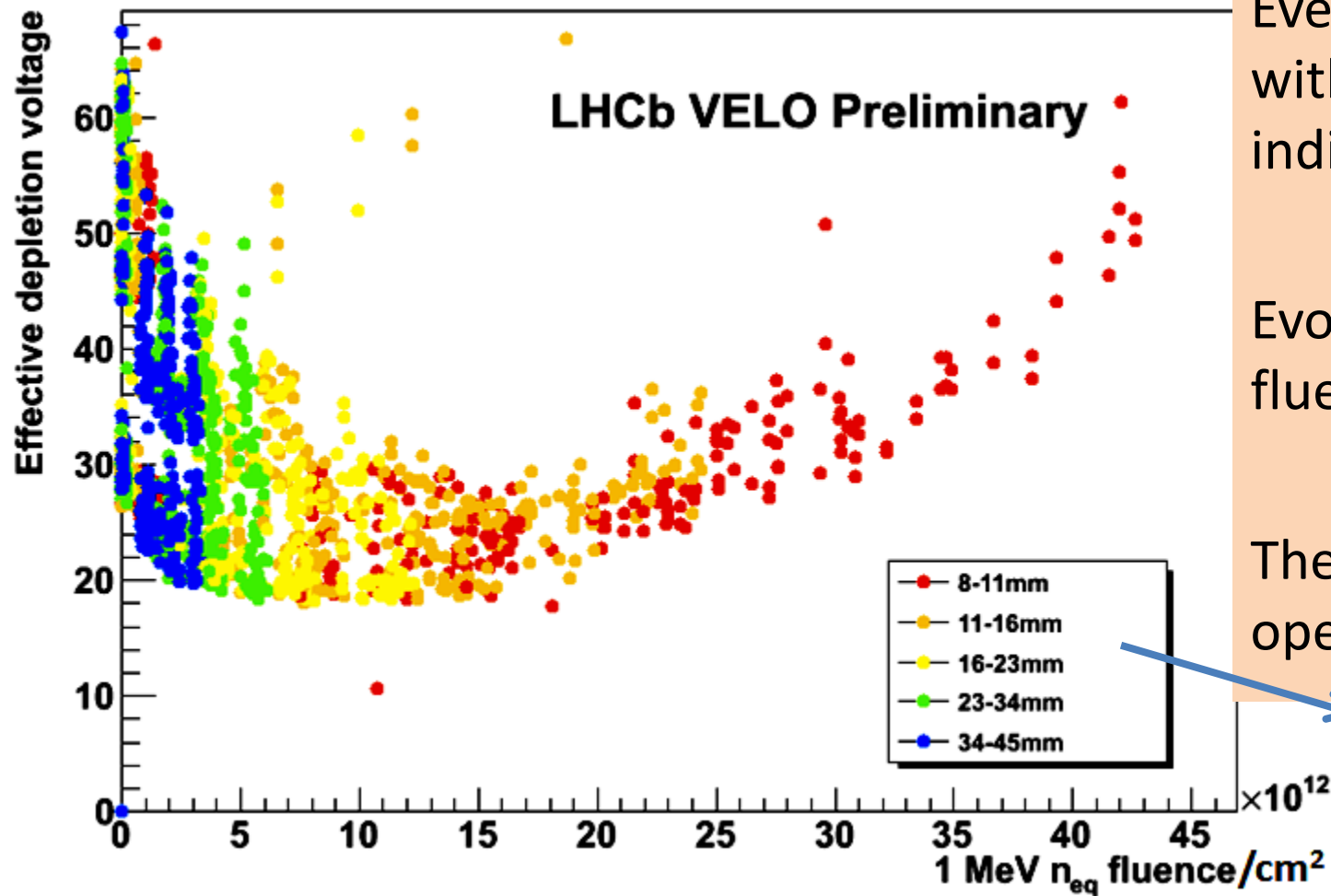
Estimate effective depletion voltage from charge collection efficiency measurements

Compare installation and current values

Overall 13V to 20V lower

Binned in radius due to variation in dose with radius

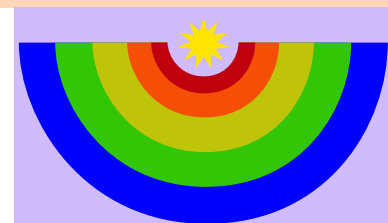
# Effective depletion voltage for all sensors with fluence by radius



Every sensor's EDV with colours indicating the radius

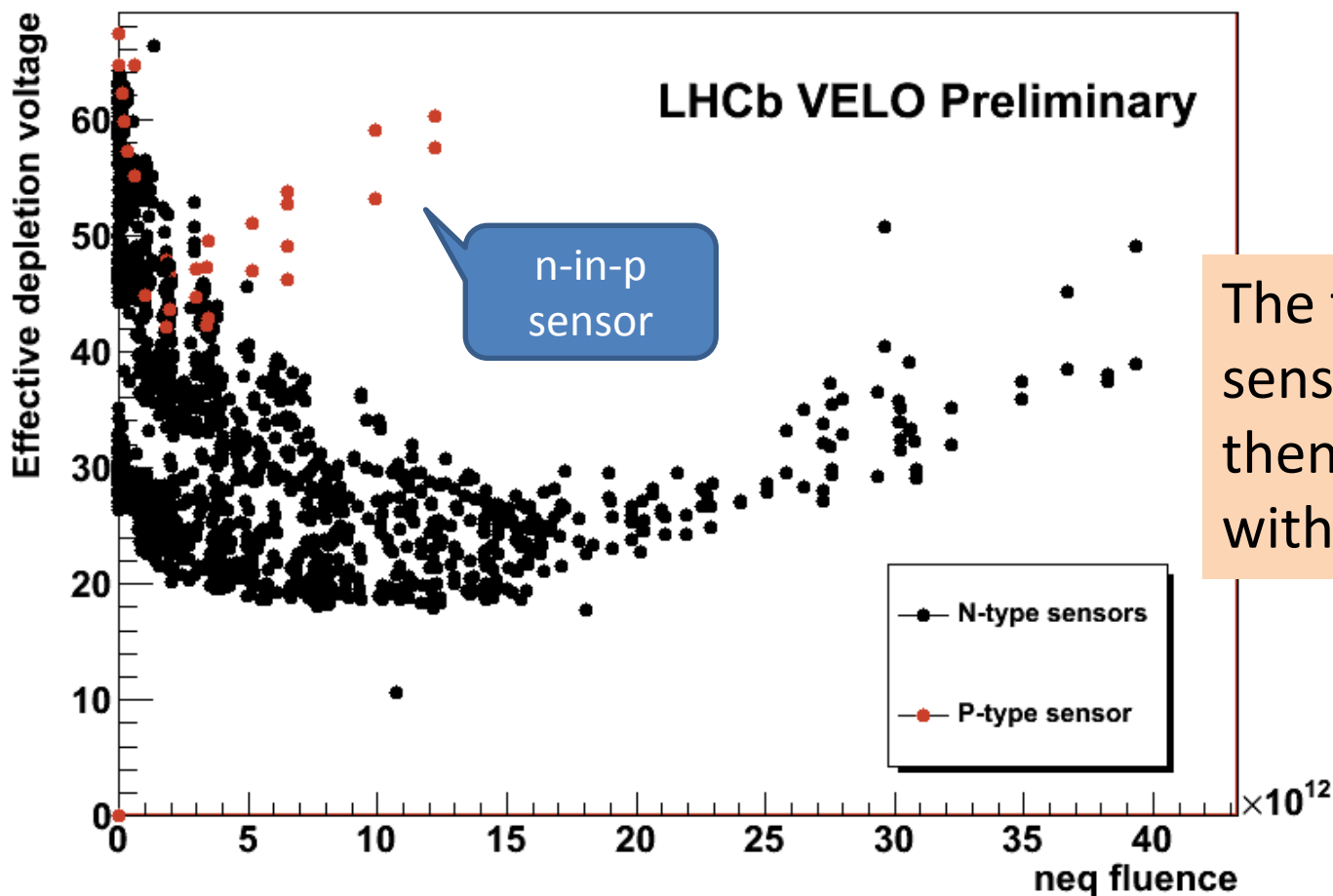
Evolution with fluence shown

The HV can be operated up to 500V



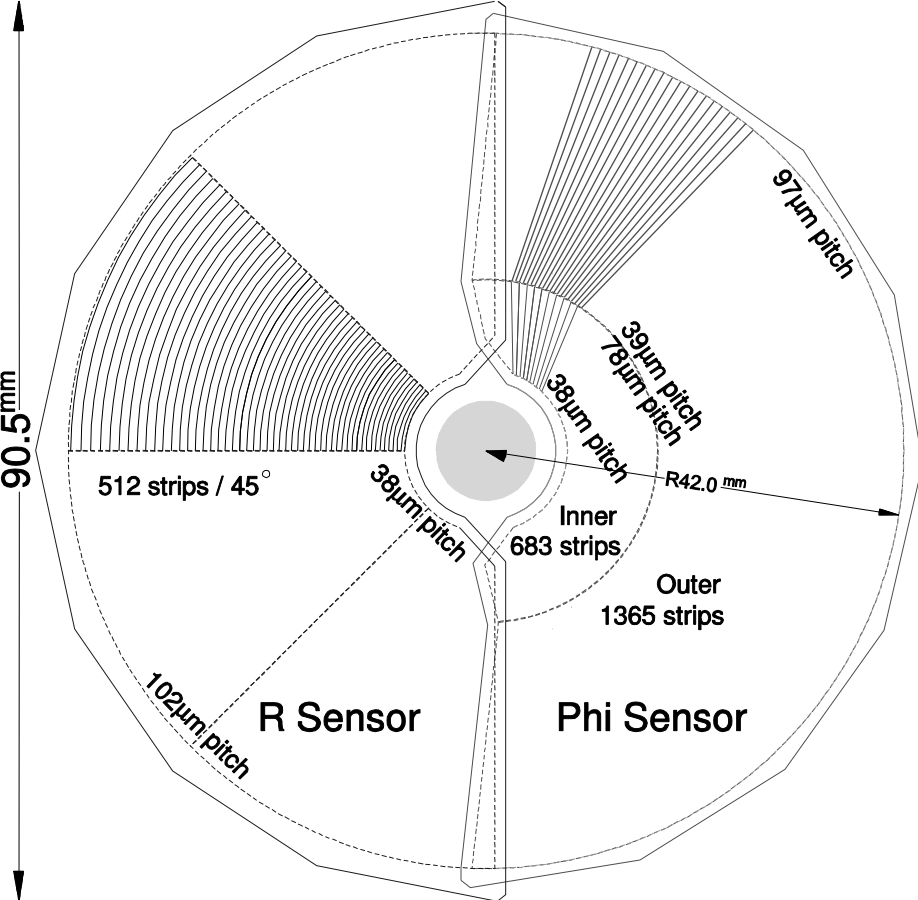
# Effective depletion voltage for all sensors with fluence by type

Effective depletion voltage vs fluence



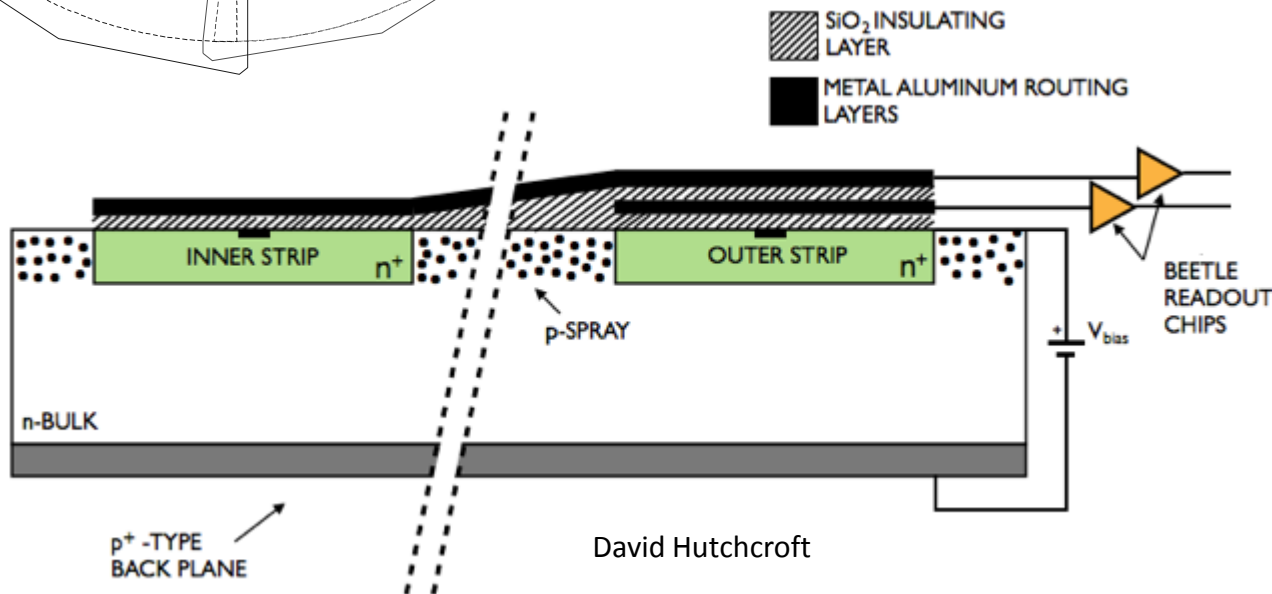
The two n-in-p sensors show a drop then rise in the EDV with fluence





# Double metal effects

- R and phi sensors need two sets of metal lines
- One to capacitively couple to the strips, the other carrying the signal to the amplifiers over the outer strips
- Phi sensors (below) second metal routing is over the outer strips



# R sensors route across the outer strips

Picture of the outer edge of the R sensor's active area

First Metal layer on top of strips

Routing Line width ~ 10  $\mu\text{m}$

Strip width ~ 38  $\mu\text{m}$

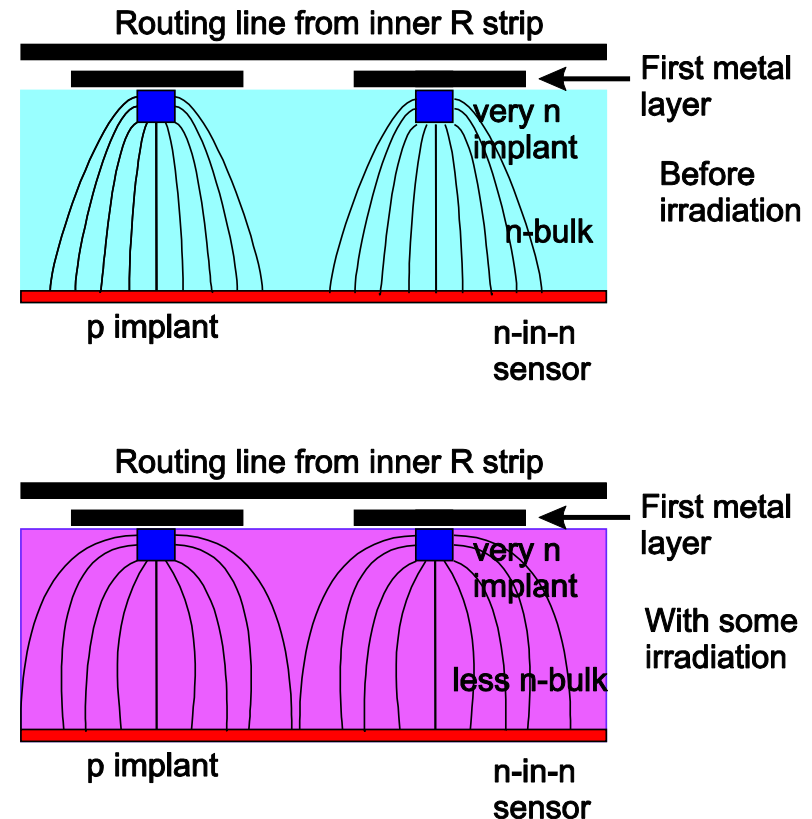
Strip pitch 101  $\mu\text{m}$

Second metal layer running across the strips

Bond pads for links to readout chips

# Coupling effects of signals in R sensors

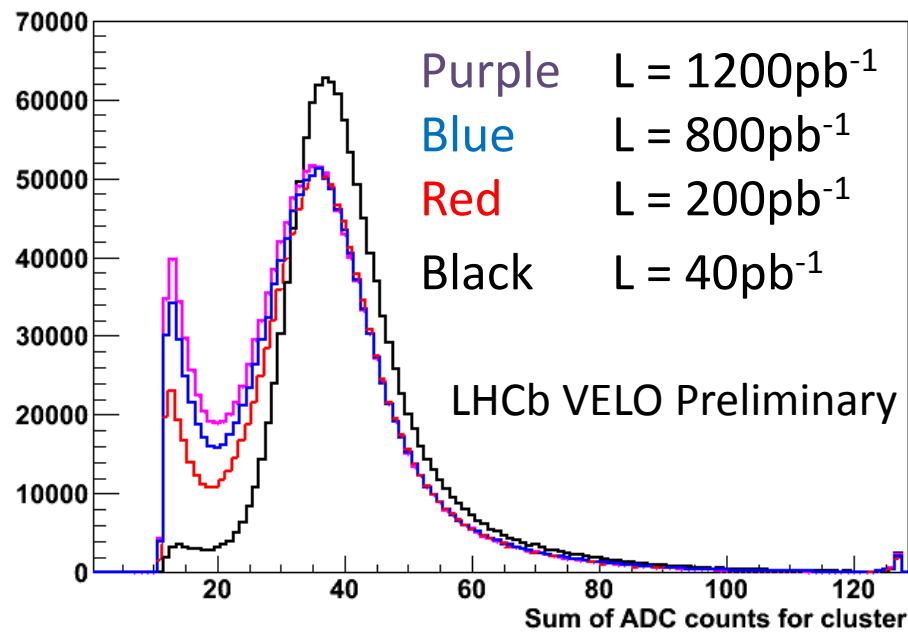
- Before irradiation there was no visible coupling to between inner and outer strips
- When a signal passes between the strips both layers of routing lines couple to the moving charge
- Before irradiation free surface charges can act as a shield as does the 1<sup>st</sup> metal layer
- After irradiation we see phantom signals in the inner strips



# Effects in data taking

Cluster on inner R strips at very low ADC counts appearing

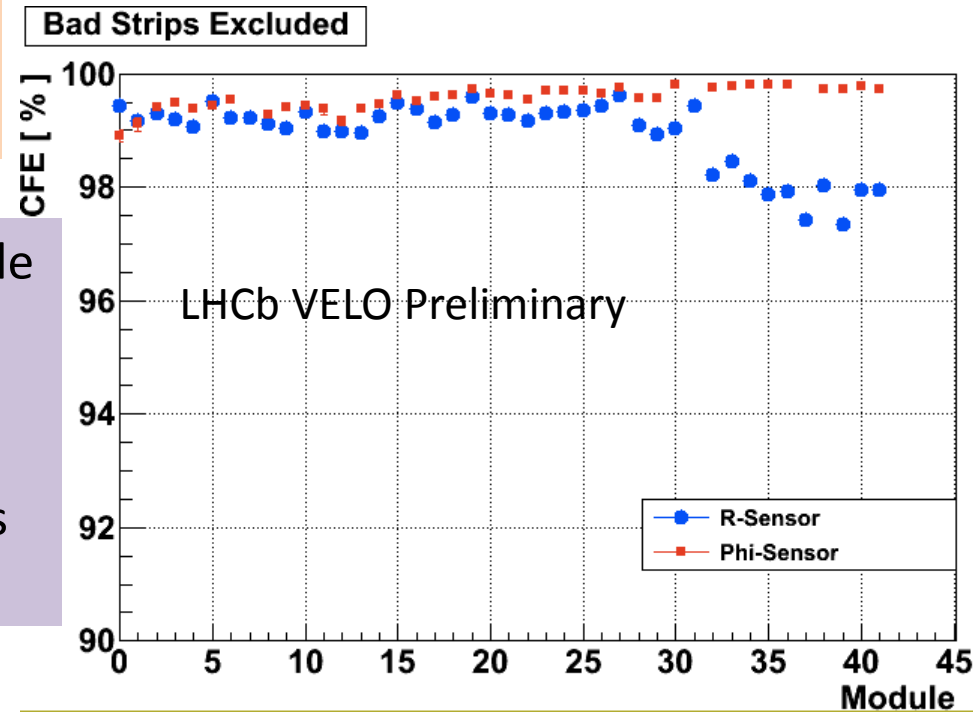
Predominately at the inner regions of the sensors, not where tracks crossed the sensors



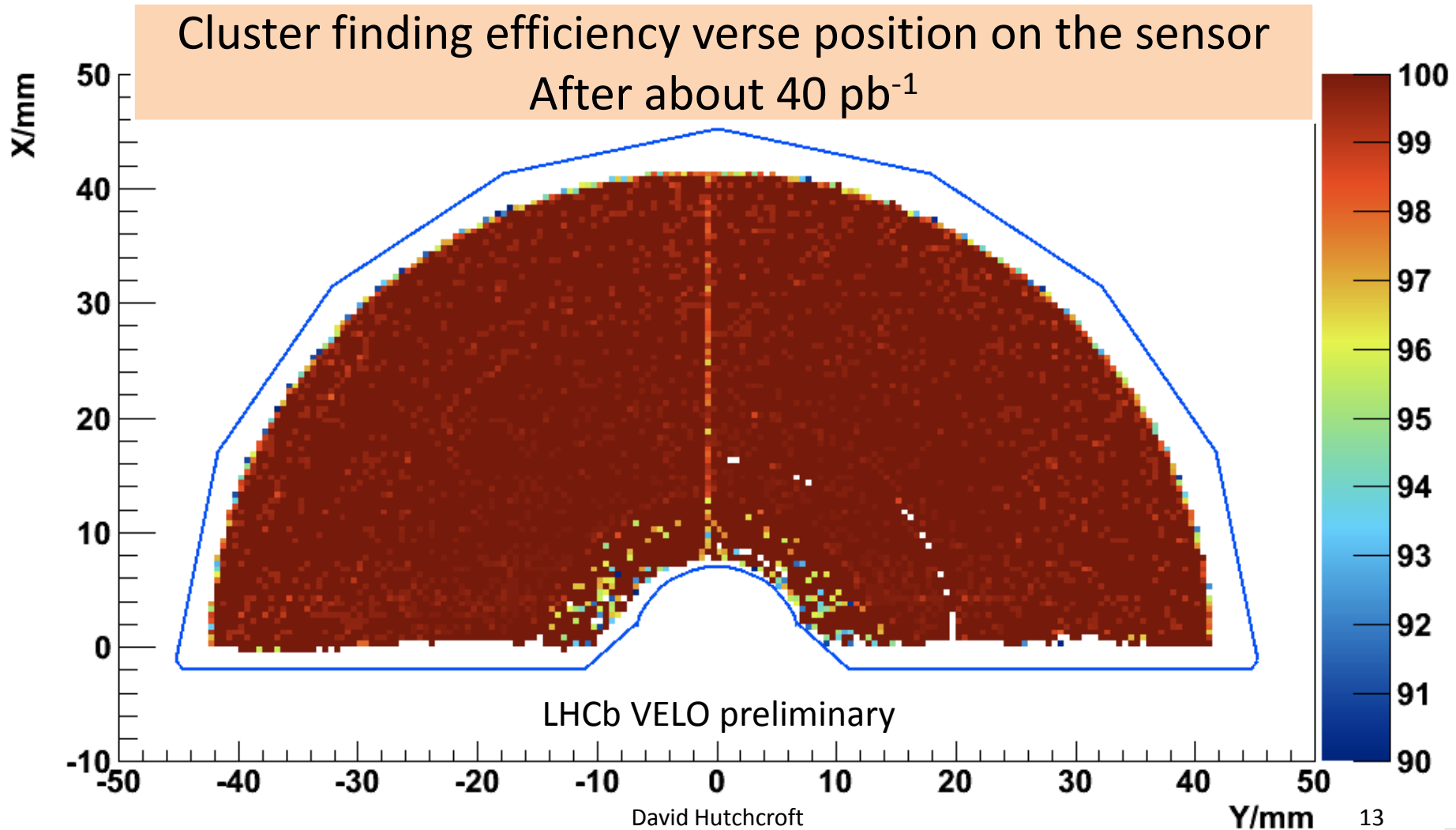
Cluster size for R sensor clusters in ADC counts for clusters not associated to tracks

Cluster finding efficiency verse module  
A reduction in the cluster finding efficiency for the R sensors

Predominately in the forward sensors and at large radius

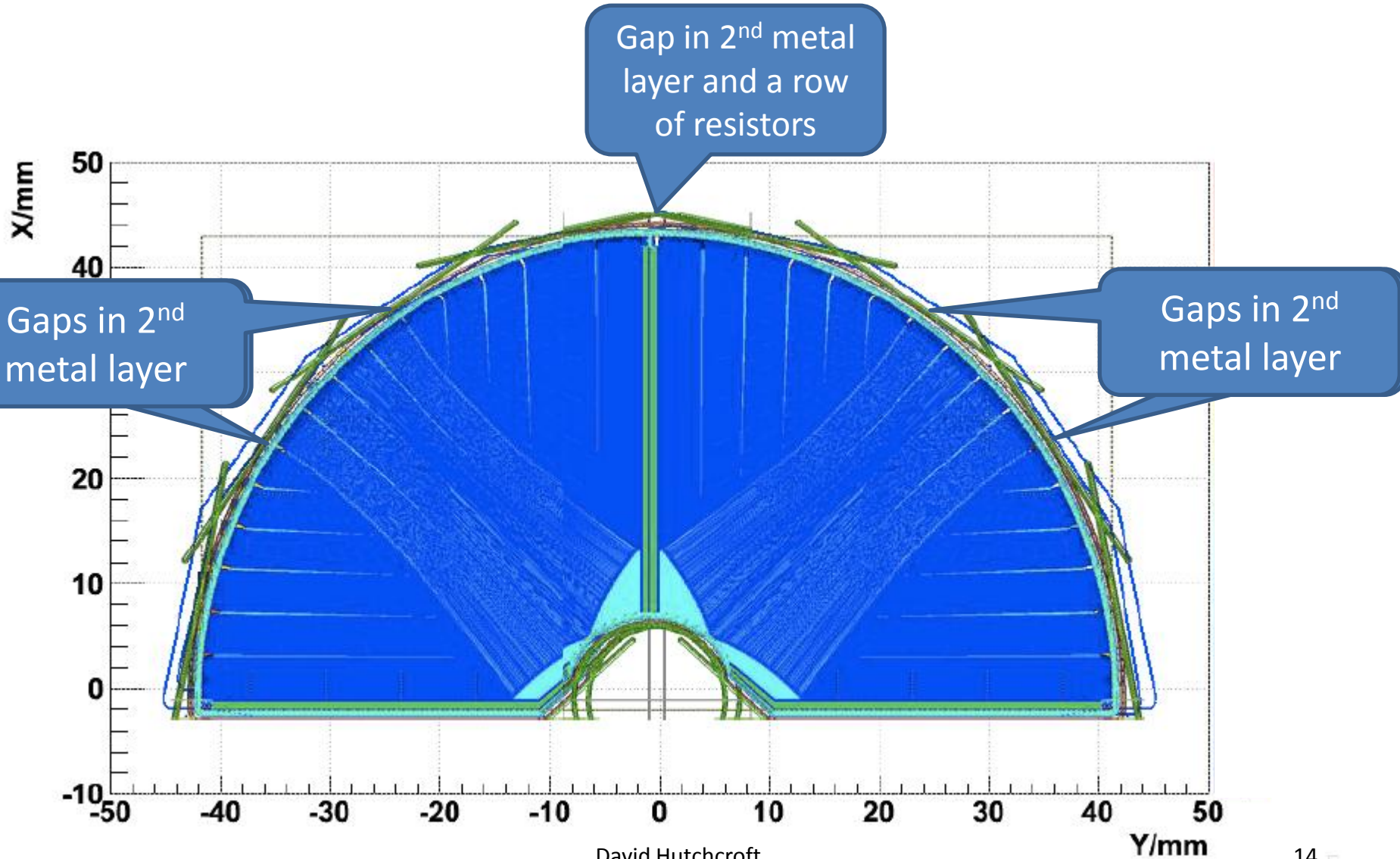


# Cluster finding efficiency 2D map for one R sensor, sensor 40



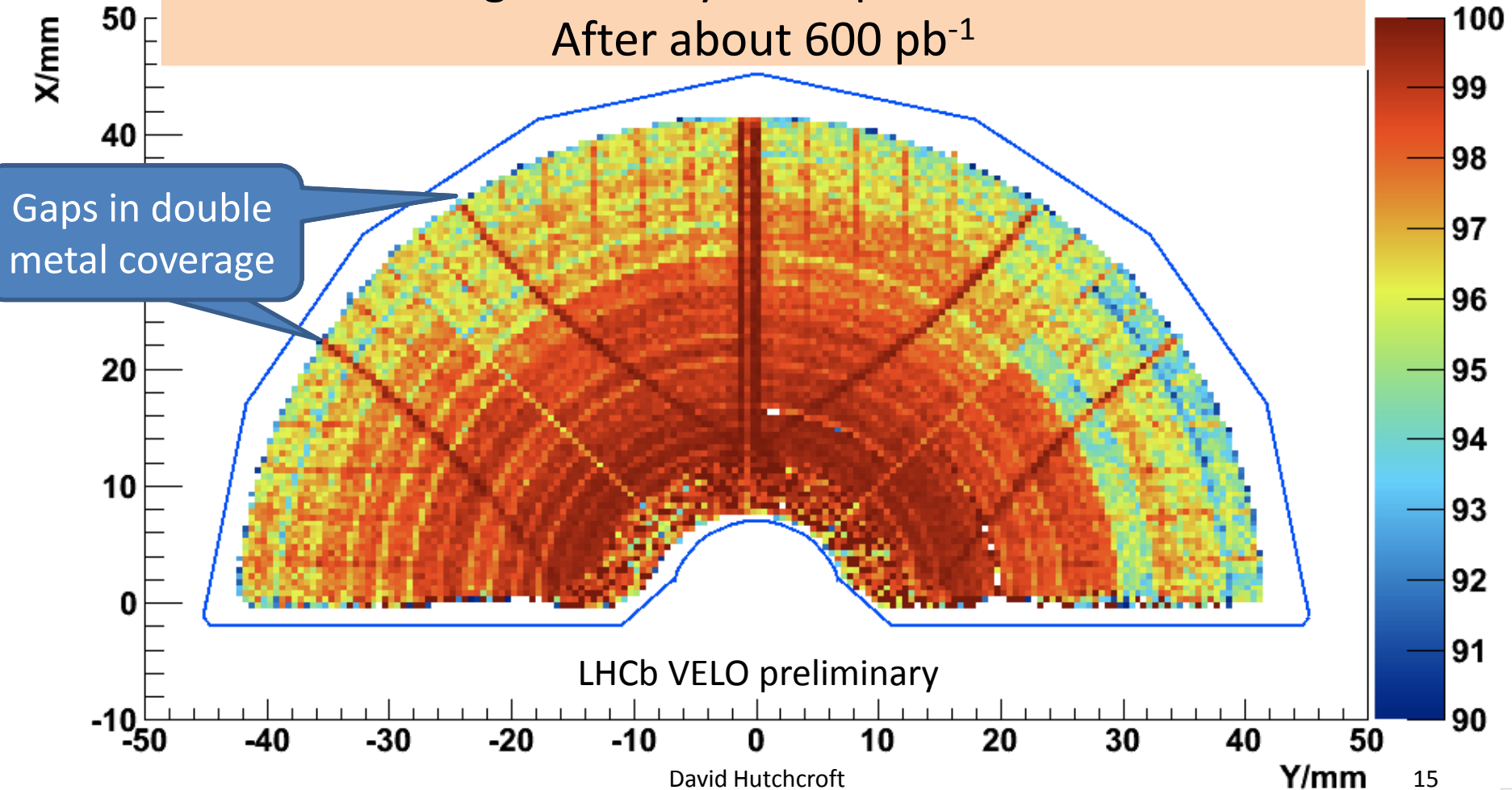


# Second metal layer layout for R sensors



# Cluster finding efficiency 2D map for one R sensor, sensor 40

Cluster finding efficiency verse position on the sensor  
After about  $600 \text{ pb}^{-1}$



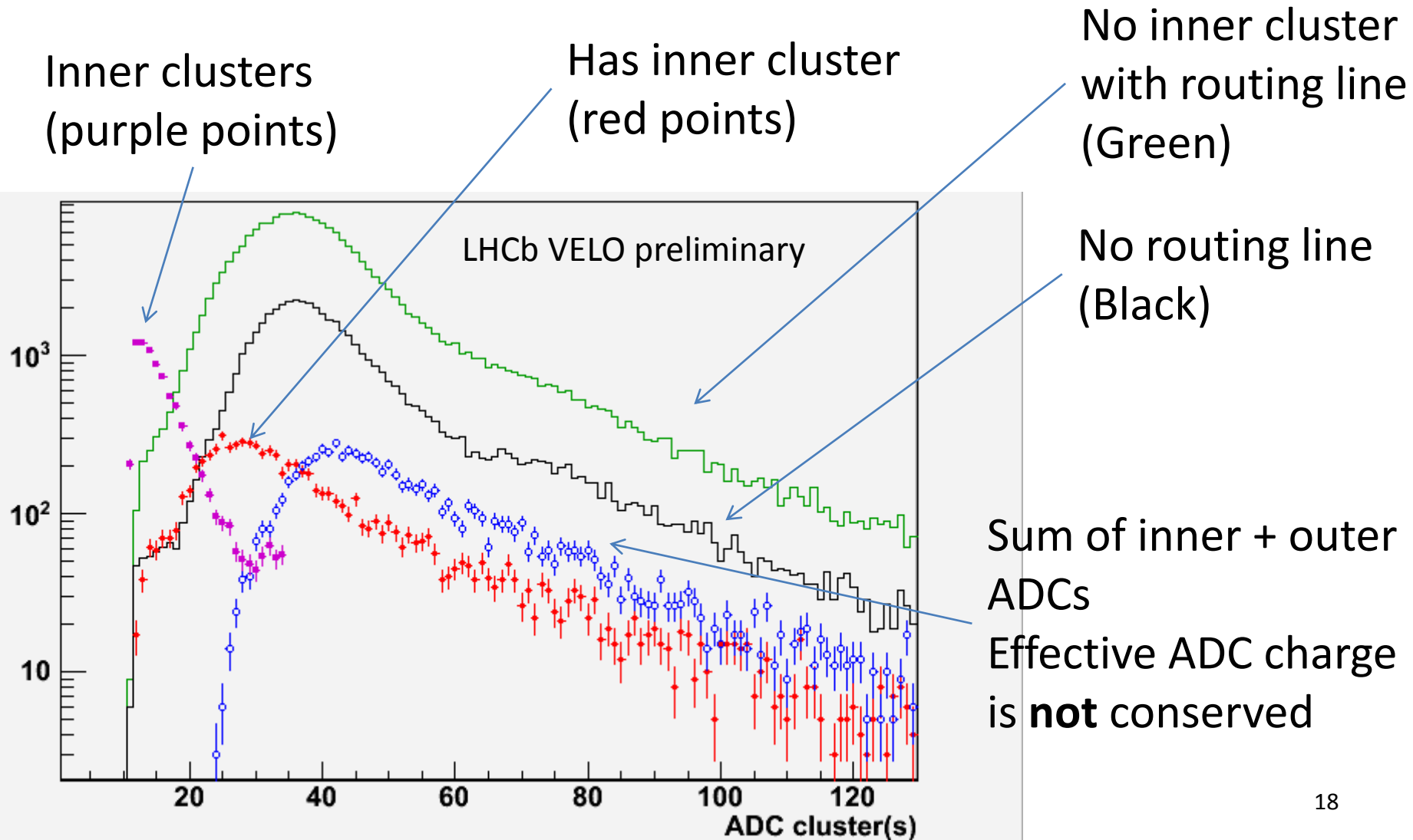
# Conclusions

- LHCb VELO detectors do see radiation damage
- Type inversion now confirmed for inner edges of sensors close to beam spot
- Leakage currents rising linearly with luminosity
  - We now always keep the detector cold to avoid unwanted annealing
- R sensors show coupling to second metal layer causing a reduction in efficiency
- Tracking efficiencies are as yet unchanged (<0.5% effects)
- Every reason to believe that we will get five more years out of these sensors



# Backup slides

# Effects of double metal effect on charge collected in ADC counts

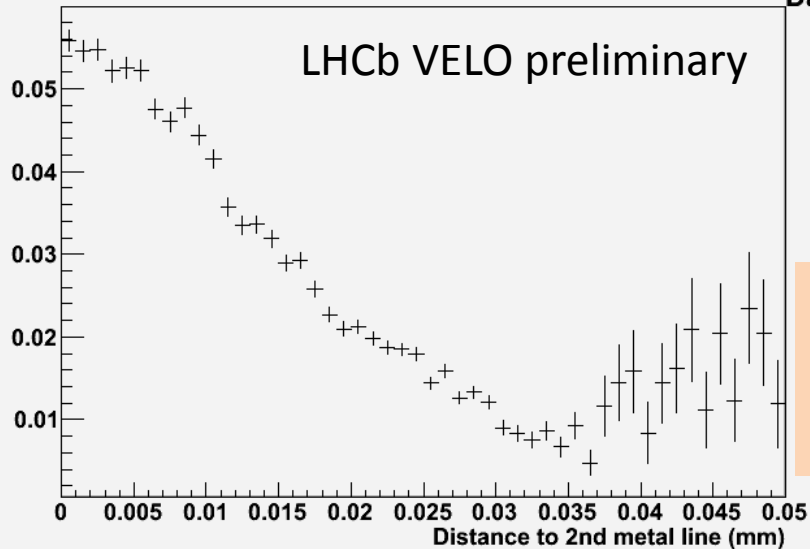


# Parameters of double metal effects

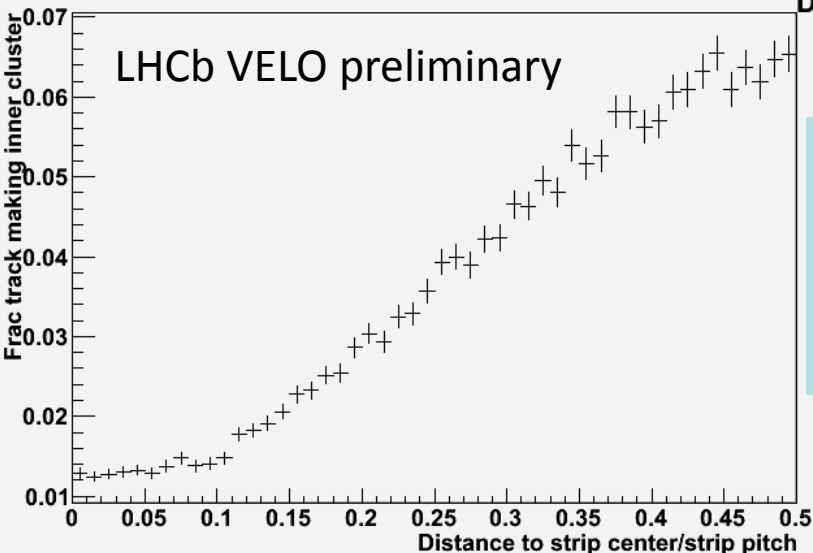
Effects of track position on coupling to second metal layer

Fraction of tracks impact points with a fake inner cluster verse distance of track to closest 2<sup>nd</sup> metal layer

fraction of inner verse M2 line to track dist(mm)



fraction of inner verse Strip to track dist(pitchFrac)



Fraction of tracks impact points with a fake inner cluster verse distance of track to centre line of the strip (1<sup>st</sup> metal layer)